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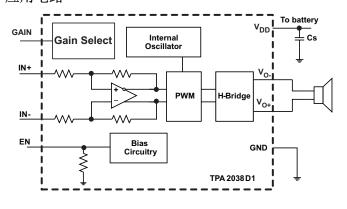
可选增益和自动恢复短路保护的 3.2W 单声道 D 类音频功率放大器

查询样品: TPA2038D1

特性

- 无滤波器单声道 **D** 类扬声器放大器
- 6dB 和 12dB 间的增益引脚选择
- 5V 电源(10% 总谐波失真 + 噪声 (THD + N)) 提供 3.2W 功率进入 4Ω 负载
- 功能强大的单声道 D 类扬声器放大器
 - 在 5V 电源提供 1.4W 功率进入 8Ω 时为 1%
 - 在 5V 电源提供 2.5W 功率进入 4Ω 时为 1%
- 集成图像抑制滤波器用于 DAC 降噪
- 20µV 低输出噪声
- 1.5mA 低静态电流
- 自动恢复短路保护
- 热过载保护
- 9 焊球, 1.21mm x 1.16mm 0.4mm 焊球间距晶圆级芯片封装 (WCSP)

应用电路



应用范围

- 无线或者蜂窝手持电话和个人数据助理(PDA)
- 便携式导航设备
- 普通便携式音频器件

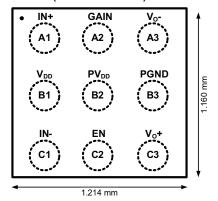
说明

TPA2038D1 是一款 3.2W 功率进入 4 欧姆负载 (10% THD) 高效无滤波器 D 类音频功率放大器。 增益引脚 将增益设定为 6dB 或 12dB。

诸如 95% 的效率, 1.5mA 静态电流, 0.5μA 关断电流, 81dB 电源抑制比 (PSRR), 20μV 输出噪声和改进的射频 (RF) 抗扰度使得 TPA2038D1 D 类放大器非常适合于蜂窝手机应用。 无接通爆音的 4ms 内启动时间。

TPA2038D1 采用 1.21mm x 1.16mm, 0.4 焊球间距晶圆级芯片封装 (WCSP)。

TPA 2038D1 9-BALL 0.4mm PITCH WAFER CHIP SCALE PACKAGE (YFF) (TOP VIEW OF PCB)





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION

T _A	PACKAGED DEVICES ⁽¹⁾	PART NUMBER (2)	SYMBOL
-40°C to 85°C	O Fall WCCD	TPA2038D1YFFR	QWK
	9-ball WCSP	TPA2038D1YFFT	QWK

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com
- (2) The YFF package is only available taped and reeled. The suffix "R" indicates a reel of 3000, the suffix "T" indicates a reel of 250.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range, T_A = 25°C (unless otherwise noted)⁽¹⁾

			VALUE	UNIT
V_{DD} , PV_{DD}	Cupply voltage	In active mode	-0.3 to 6.0	V
	Supply voltage	In shutdown mode	-0.3 to 6.0	V
VI	Input voltage	EN, IN+, IN-	-0.3 to V _{DD} + 0.3	V
R _L	Minimum load re	sistance	3.2	Ω
	Output continuous total power dissipation		See Dissipation Rating Table	
T _A	Operating free-a	r temperature range	-40 to 85	°C
TJ	Operating junction	on temperature range	-40 to 150	°C
T _{stg}	Storage tempera	ture range	-65 to 85	°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods may affect device reliability.

DISSIPATION RATINGS

PACKAGE	DERATING FACTOR ⁽¹⁾	T _A < 25°C	T _A = 70°C	T _A = 85°C
YFF (WCSP)	4.2 mW/°C	525 mW	336 mW	273 mW

⁽¹⁾ Derating factor measure with high K board.

RECOMMENDED OPERATING CONDITIONS

				MIN	MAX	UNIT
V _{DD} , PV _{DD}	Class-D supply voltage				5.5	V
V_{IH}	High-level input voltage	EN, GAIN		1.3		V
V_{IL}	Low-level input voltage	EN, GAIN			0.35	V
V_{IC}	Common mode input voltage range	V _{DD} = 2.5 V, 5.5 V, CMRR ≥ 49 dB		0.75	V _{DD} -1.1	V
T _A	Operating free-air temperature				85	°C

GAIN SETTING

GAIN PIN	GAIN SETTING
GND	12 dB
VDD	6 dB



ELECTRICAL CHARACTERISTICS

 $PVDD = VDD = 3.6 \text{ V}, T_A = 25^{\circ}\text{C}$ (unless otherwise noted)

·	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
V _{OS}	Output offset voltage (measured differentially)	VDD = 2.5 V to 5.5 V, GAIN = VDD		1	5	mV	
I _{IH}	High-level EN input current	VDD = 5.5 V, EN = GAIN = 5.5 V			50	μΑ	
I _{IL}	Low-level EN input current	VDD = 5.5 V, EN = GAIN = 0 V			1	μΑ	
		VDD = 5.5 V, no load		1.8	2.5		
I _(Q)	Quiescent current	VDD = 3.6 V, no load		1.5	2.3	mA	
		VDD = 2.5 V, no load		1.3	2.1		
I _(SD)	Shutdown current	EN = 0.35 V, VDD = 3.6 V		0.1	2	μΑ	
R _{O, SD}	Output impedance in shutdown mode	EN = 0.35 V		2		kΩ	
f _(SW)	Switching frequency	VDD = 2.5 V to 5.5 V	250	300	350	kHz	
A _V	Gain	GAIN = 0 V	11.5	12	12.5	ı.	
		GAIN = VDD	5.5	6	6.5	dB	
R _{EN}	Resistance from EN to GND			300		kΩ	
		A _V = 6 dB; EN = VDD		150			
R _{IN}	Single-ended input resistance	A _V = 12 dB; EN = VDD	75		kΩ		
		EN = 0.35 V		75			

OPERATING CHARACTERISTICS

PVDD = VDD = 3.6 V, $A_V = 6$ dB, $T_A = 25$ °C, $R_L = 8$ Ω (unless otherwise noted)

	PARAMETER	TEST CONDITION	ONS	MIN TYP	MAX	UNIT
			V _{DD} = 5 V	3.24		
		THD + N = 10%, f = 1 kHz, $R_1 = 4 \Omega$	V _{DD} = 3.6 V	1.62		W
		11 - 4 22	$V_{DD} = 2.5 \text{ V}$	0.70		
Po			$V_{DD} = 5 V$	2.57		W
		THD + N = 1%, f = 1 kHz, $R_1 = 4 \Omega$	$V_{DD} = 3.6 \text{ V}$	1.32		
	Output a succe	11 - 4 22	V _{DD} = 2.5 V	0.57		
	Output power		V _{DD} = 5 V	1.80		
		THD + N = 10%, f = 1 kHz, $R_L = 8 \Omega$	$V_{DD} = 3.6 \text{ V}$	0.91		W
			$V_{DD} = 2.5 \text{ V}$	0.42		
		THD + N = 1%, f = 1 kHz, R _L = 8 Ω	V _{DD} = 5 V	1.46		W
			V _{DD} = 3.6 V	0.74		
			V _{DD} = 2.5 V	0.33		
	Output voltage noise, A _V = 6 dB	V _{DD} = 3.6 V, Inputs AC	A-weighting	20		μV _{RMS}
_		grounded with $C_1 = 2 \mu F$, = 100 J	No weighting	26		
E _N	Output voltage raise A 42 dB	1 = 20 112 to 20 KHZ	A-weighting	27		
	Output voltage noise, A _V = 12 dB		No weighting	36		
		VDD = 5.0 V, P _O = 1.0 W, f =	1 kHz, R _L = 8 Ω	0.12%		
		VDD = 3.6 V, P _O = 0.5 W, f =	0.05%			
TUD.N	Total harmonic distantan also sates	VDD = 2.5 V, P _O = 0.2 W, f =	0.05%			
THD+N	Total harmonic distortion plus noise	VDD = 5.0 V, P _O = 2.0 W, f =	1 kHz, R _L = 4 Ω	0.32%		
		VDD = 3.6 V, P _O = 1.0 W, f =	0.11%			
		VDD = 2.5 V, P _O = 0.4 W, f =	0.12%			
DODD	AC nouse supply rejection refi-	A_V = 6 dB, Inputs AC grounded with C_I = 2 μ F, 200 mV _{pp} ripple, f = 217 Hz		81		٩D
PSRR	AC power supply rejection ratio	$A_V = 12$ dB, Inputs AC ground $C_I = 2 \mu F$, 200 mV _{pp} ripple, f =	82		dB	



OPERATING CHARACTERISTICS (continued)

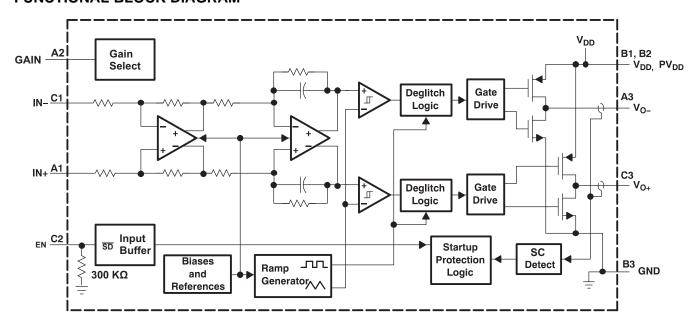
PVDD = VDD = 3.6 V, A_V = 6 dB, T_A = 25°C, R_L = 8 Ω (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
CMRR Common mode rejection ratio		$A_V = 6 \text{ dB}, V_{IC} = 200 \text{ mV}_{PP}, f = 217 \text{ Hz}$		79		dB
		$A_V = 12 \text{ dB}, V_{IC} = 200 \text{ mV}_{PP}, f = 217 \text{ Hz}$		77		uБ
T _{SU}	Startup time from shutdown			4		ms
		V _{O+} shorted to VDD				
		V _O _ shorted to VDD		2		
I _{SC}	Short circuit protection threshold	V _{O+} shorted to GND				Α
		V _O - shorted to GND				
		V _{O+} shorted to V _{O-}				
T _{AR}	Overcurrent recovery time	VDD = 2.5 V to 5.5 V		100		ms

Terminal Functions

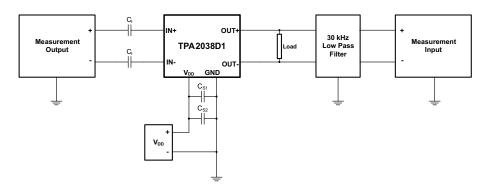
TEI	TERMINAL		MINAL I/O		DESCRIPTION
NAME	WCSP BALL	1/0	DESCRIPTION		
IN+	A1	Ι	Positive audio input.		
GAIN	A2	Ι	Gain select. Set to GND for 12 dB; set to VDD for 6 dB.		
V _{O-}	А3	0	Negative audio output.		
VDD	B1	-	Power supply terminal. Connect to PVDD using a direct connection.		
PVDD	B2	- 1	Class-D output power supply. Connect to VDD using a direct connection.		
GND	B3	Ι	Ground.		
IN-	C1	_	Negative audio input.		
EN	C2	_	Enable. Set to logic high to enable device.		
V _{O+}	C3	0	Positive audio output.		

FUNCTIONAL BLOCK DIAGRAM





TEST SETUP FOR GRAPHS



- 1. C_1 was shorted for any common-mode input voltage measurement. All other measurements were taken with C_1 = 0.1 μ F (unless otherwise noted).
- 2. C_{S1} = 0.1 μF is placed very close to the device. The optional C_{S2} = 10 μF is used for datasheet graphs.
- 3. The 30 kHz low-pass filter is required even if the analyzer has an internal low-pass filter. An RC low-pass filter (1 k Ω , 4700 pF) is used on each output for the data sheet graphs.

NSTRUMENTS

TYPICAL CHARACTERISTICS

PVDD = VDD = 3.6 V, C_{I} = 0.1 μ F, C_{S1} = 0.1 μ F, C_{S2} = 10 μ F, T_{A} = 25°C, R_{L} = 8 Ω (unless otherwise noted)

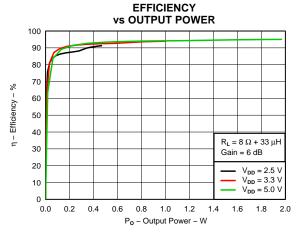


Figure 1.

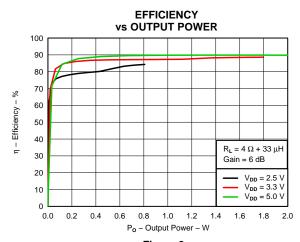
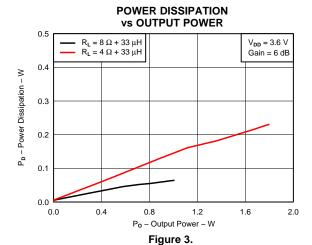
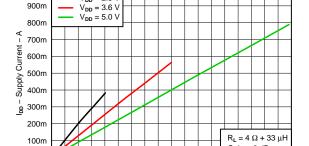


Figure 2.





 $V_{DD} = 2.5 \text{ V}$

900m

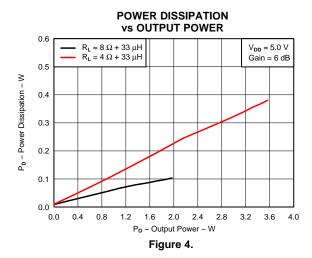
n

SUPPLY CURRENT

vs OUTPUT POWER

Po - Output Power - W Figure 5.

0.0 0.2 0.4 0.6 0.8 1.0 1.2 1.4 1.6 1.8 2.0 2.2 2.4 2.6 2.8 3.0 3.2 3.4 3.6



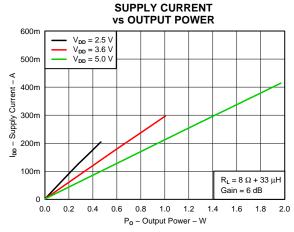
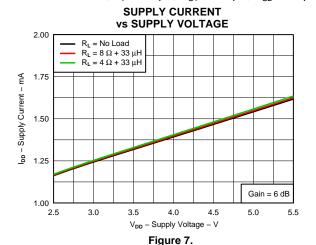


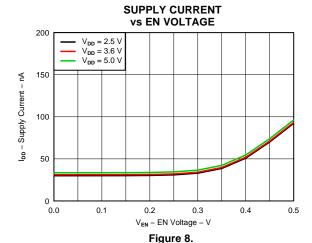
Figure 6.

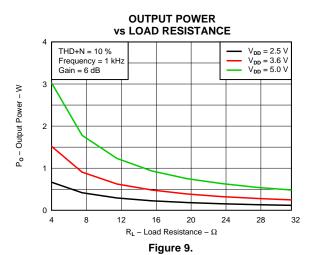


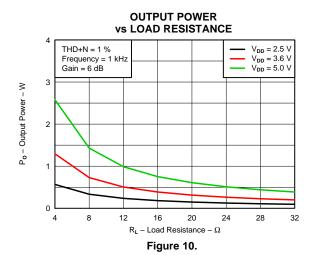
TYPICAL CHARACTERISTICS (continued)

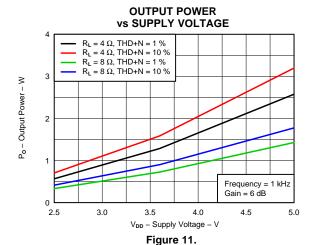
 $PVDD = VDD = 3.6 \text{ V, } C_{l} = 0.1 \text{ } \mu\text{F, } C_{S1} = 0.1 \text{ } \mu\text{F, } C_{S2} = 10 \text{ } \mu\text{F, } T_{A} = 25^{\circ}\text{C, } R_{L} = 8 \text{ } \Omega \text{ (unless otherwise noted)}$











TEXAS INSTRUMENTS

TYPICAL CHARACTERISTICS (continued)

PVDD = VDD = 3.6 V, C_{l} = 0.1 μ F, C_{S1} = 0.1 μ F, C_{S2} = 10 μ F, T_{A} = 25°C, R_{L} = 8 Ω (unless otherwise noted)

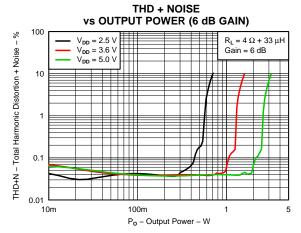


Figure 12.

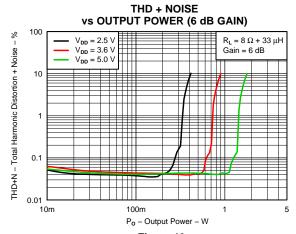


Figure 13.

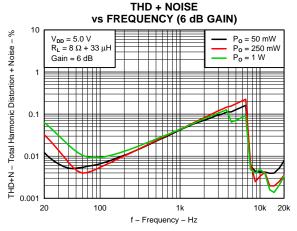


Figure 14.

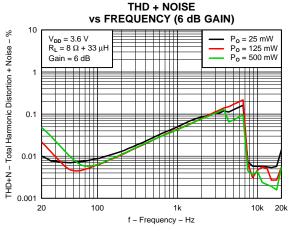
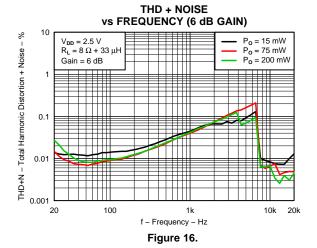


Figure 15.

THD + NOISE

vs FREQUENCY (6 dB GAIN)



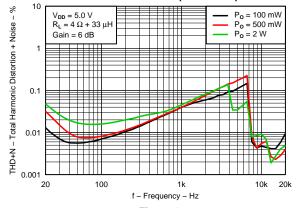


Figure 17.



TYPICAL CHARACTERISTICS (continued)

 $PVDD = VDD = 3.6 \text{ V, } C_{l} = 0.1 \text{ } \mu\text{F, } C_{S1} = 0.1 \text{ } \mu\text{F, } C_{S2} = 10 \text{ } \mu\text{F, } T_{A} = 25^{\circ}\text{C, } R_{L} = 8 \text{ } \Omega \text{ (unless otherwise noted)}$

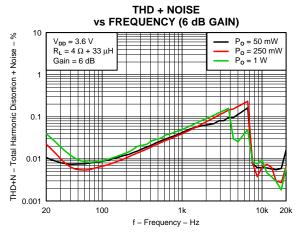


Figure 18.

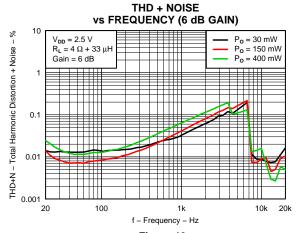


Figure 19.

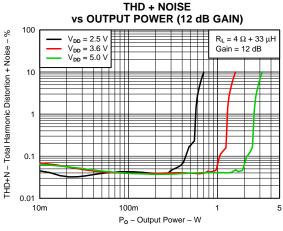


Figure 20.

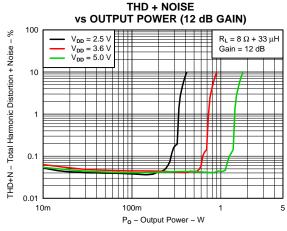
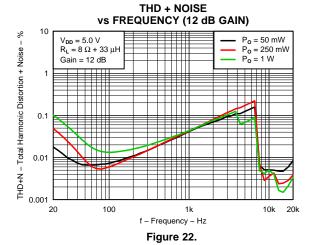


Figure 21.

THD + NOISE



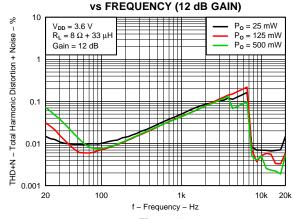


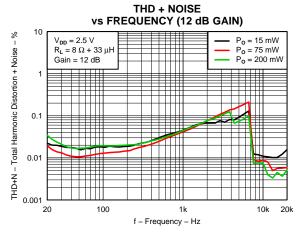
Figure 23.

INSTRUMENTS

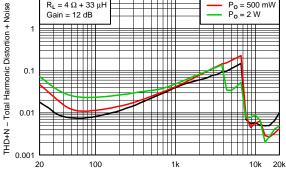
 $P_0 = 100 \text{ mW}$

TYPICAL CHARACTERISTICS (continued)

PVDD = VDD = 3.6 V, C_{l} = 0.1 μ F, C_{S1} = 0.1 μ F, C_{S2} = 10 μ F, T_{A} = 25°C, R_{L} = 8 Ω (unless otherwise noted)



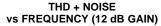
 $V_{DD} = 5.0 \text{ V}$ $R_L = 4 \Omega + 33 \mu \text{H}$ P_o = 500 mW Gain = 12 dB $P_0 = 2 W$

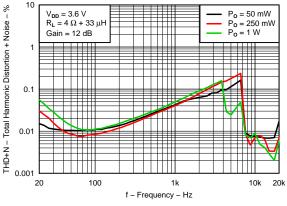


THD + NOISE vs FREQUENCY (12 dB GAIN)

Figure 24.

Figure 25.





THD + NOISE vs FREQUENCY (12 dB GAIN)

f - Frequency - Hz

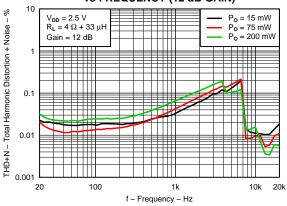
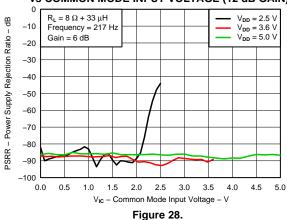


Figure 26.

Figure 27.

POWER SUPPLY REJECTION RATIO vs COMMON MODE INPUT VOLTAGE (12 dB GAIN)



POWER SUPPLY REJECTION RATIO vs FREQUENCY (6 dB GAIN)

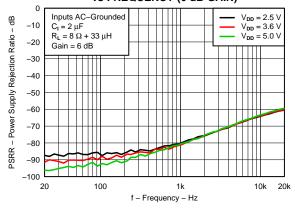


Figure 29.



TYPICAL CHARACTERISTICS (continued)

 $PVDD = VDD = 3.6 \text{ V, } C_{l} = 0.1 \text{ } \mu\text{F, } C_{S1} = 0.1 \text{ } \mu\text{F, } C_{S2} = 10 \text{ } \mu\text{F, } T_{A} = 25^{\circ}\text{C, } R_{L} = 8 \text{ } \Omega \text{ (unless otherwise noted)}$

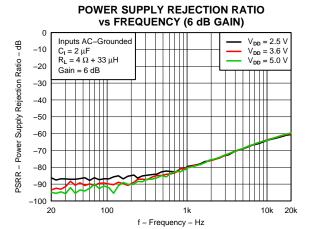


Figure 30.

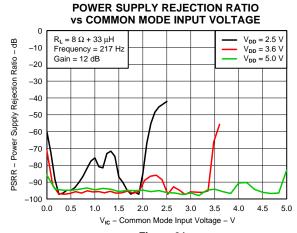


Figure 31.

POWER SUPPLY REJECTION RATIO vs FREQUENCY (12 dB GAIN)

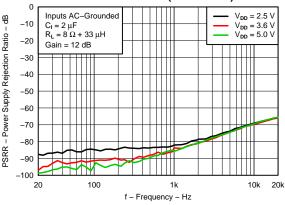


Figure 32.

POWER SUPPLY REJECTION RATIO vs FREQUENCY (12 dB GAIN)

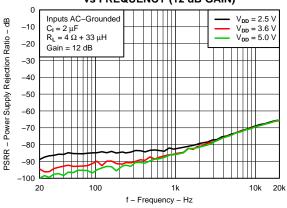


Figure 33.

COMMON MODE REJECTION RATIO VS COMMON MODE INPUT VOLTAGE (6 dB GAIN)

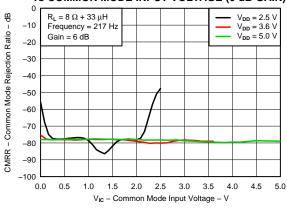


Figure 34.

COMMON MODE REJECTION RATIO vs FREQUENCY (6 dB GAIN)

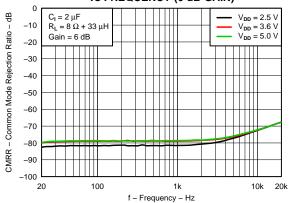


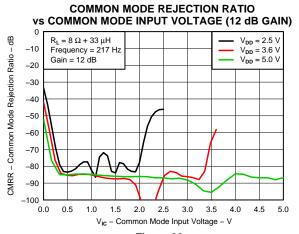
Figure 35.

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TYPICAL CHARACTERISTICS (continued)

PVDD = VDD = 3.6 V, C_{I} = 0.1 μF, C_{S1} = 0.1 μF, C_{S2} = 10 μF, T_{A} = 25°C, R_{L} = 8 Ω (unless otherwise noted)



COMMON MODE REJECTION RATIO vs FREQUENCY (12 dB GAIN)

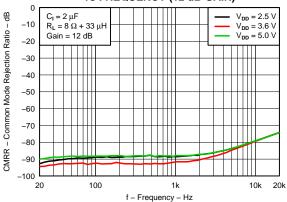
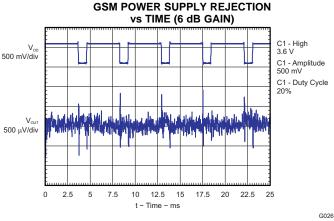


Figure 36.

Figure 37.



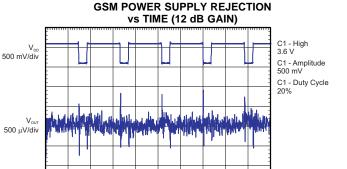
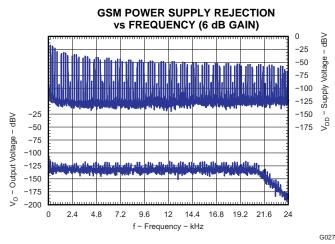
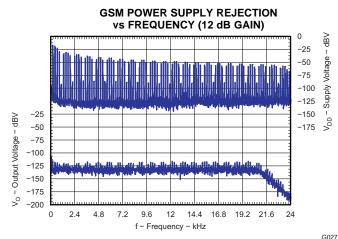


Figure 38. Figure 39.

2.5 5 7.5 10 12.5 15 17.5 20





t - Time - ms

Figure 40. Figure 41.



APPLICATION INFORMATION

SHORT CIRCUIT AUTO-RECOVERY

When a short-circuit event occurs, the TPA2038D1 goes to shutdown mode and activates the integrated autorecovery process whose aim is to return the device to normal operation once the short-circuit is removed. This process repeatedly examines (once every 100 ms) whether the short-circuit condition persists, and returns the device to normal operation immediately after the short-circuit condition is removed. This feature helps protect the device from large currents and maintain a good long-term reliability.

INTEGRATED IMAGE REJECT FILTER FOR DAC NOISE REJECTION

In applications which use a DAC to drive Class-D amplifiers, out-of-band noise energy present at the DAC's image frequencies fold back into the audio-band at the output of the Class-D amplifier. An external low-pass filter is often placed between the DAC and the Class-D amplifier in order to attenuate this noise.

The TPA2038D1 has an integrated Image Reject Filter with a low-pass cutoff frequency of 130 kHz, which significantly attenuates this noise. Depending on the system noise specification, the integrated Image Reject Filter may help eliminate external filtering, thereby saving board space and component cost.

COMPONENT SELECTION

Figure 42 shows the TPA2038D1 typical schematic with differential inputs, while Figure 43 shows the TPA2038D1 with differential inputs and input capacitors. Figure 44 shows the TPA2038D1 with a single-ended input.

Decoupling Capacitors (C_{S1}, C_{S2})

The TPA2038D1 is a high-performance class-D audio amplifier that requires adequate power supply decoupling to ensure the efficiency is high and total harmonic distortion (THD) is low. For higher frequency transients, spikes, or digital hash on the line, a good low equivalent-series-resistance (ESR) ceramic capacitor $C_{S1}=0.1~\mu\text{F}$, placed as close as possible to the device V_{DD} lead works best. Placing C_{S1} close to the TPA2038D1 is important for the efficiency of the class-D amplifier, because any resistance or inductance in the trace between the device and the capacitor can cause a loss in efficiency. For filtering lower-frequency noise signals, a 10 μF or greater capacitor (C_{S2}) placed near the audio power amplifier would also help, but it is not required in most applications because of the high PSRR of this device. Typically, the smaller the capacitor's case size, the lower the inductance and the closer it can be placed to the TPA2038D1. X5R and X7R dielectric capacitors are recommended for both C_{S1} and C_{S2} .

Input Capacitors (C_I)

The TPA2038D1 does not require input coupling capacitors if the design uses a differential source that is biased within the common-mode input voltage range. That voltage range is listed in the Recommended Operating Conditions table. If the input signal is not biased within the recommended common-mode input range, such as in needing to use the input as a high pass filter, shown in Figure 43, or if using a single-ended source, shown in Figure 44, input coupling capacitors are required. The same value capacitors should be used on both IN+ and IN- for best pop performance. The 3 dB high-pass cutoff frequency f_C of the filter formed by the input coupling capacitor C_I and the input resistance R_I (typically 150 k Ω) of the TPA2038D1 is given by Equation 1:

$$f_{C} = \frac{1}{\left(2\pi R_{l}C_{l}\right)} \tag{1}$$

The value of the input capacitor is important to consider as it directly affects the bass (low frequency) performance of the circuit. Speaker response may also be taken into consideration when setting the corner frequency using input capacitors. Solving for the input coupling capacitance, we get:

$$C_{I} = \frac{1}{\left(2\pi R_{I} f_{C}\right)} \tag{2}$$

If the corner frequency is within the audio band, the capacitors should have a tolerance of $\pm 10\%$ or better, because any mismatch in capacitance causes an impedance mismatch at the corner frequency and below.



For a flat low-frequency response, use large input coupling capacitors (0.1 μF or larger). X5R and X7R dielectric capacitors are recommended.

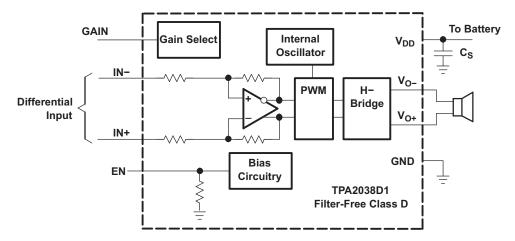


Figure 42. Typical TPA2038D1 Application Schematic With DC-coupled Differential Input

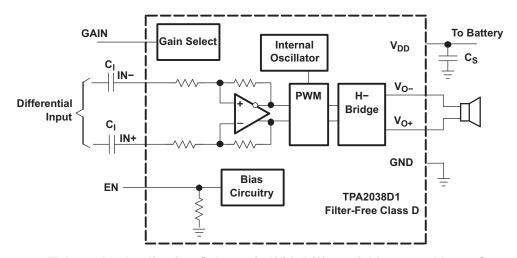


Figure 43. TPA2038D1 Application Schematic With Differential Input and Input Capacitors

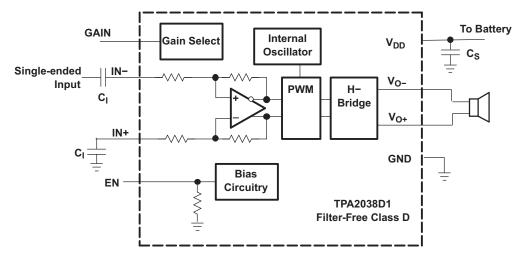


Figure 44. TPA2038D1 Application Schematic With Single-Ended Input



EFFICIENCY AND THERMAL INFORMATION

The maximum ambient operating temperature of the TPA2038D1 depends on the load resistance, power supply voltage and heat-sinking ability of the PCB system. The derating factor for the YFF package is shown in the dissipation rating table. Converting this to θ_{IA} :

$$\theta_{\text{JA}} = \frac{1}{\text{Derating Factor}}$$
 (3)

Given θ_{JA} (from the Package Dissipation ratings table), the maximum allowable junction temperature (from the Absolute Maximum ratings table), and the maximum internal dissipation (from Power Dissipation vs Output Power figures) the maximum ambient temperature can be calculated with the following equation. Note that the units on these figures are Watts RMS. Because audio contains crest factors (ratio of peak power to RMS power) from 9–15 dB, thermal limitations are not usually encountered.

$$T_{A}Max = T_{J}Max - \theta_{JA}P_{Dmax}$$
 (4)

The TPA2038D1 is designed with thermal protection that turns the device off when the junction temperature surpasses 150°C to prevent damage to the IC. Note that the use of speakers less resistive than 4 Ω (typ) is not advisable. Below 4 Ω (typ) the thermal performance of the device dramatically reduces because of increased output current and reduced amplifier efficiency. The Absolute Maximum rating of 3.2 Ω covers the manufacturing tolerance of a 4 Ω speaker and speaker impedance decrease due to frequency. θ_{JA} is a gross approximation of the complex thermal transfer mechanisms between the device and its ambient environment. If the θ_{JA} calculation reveals a potential problem, a more accurate estimate should be made.

WHEN TO USE AN OUTPUT FILTER

Design the TPA2038D1 without an Inductor / Capacitor (LC) output filter if the traces from the amplifier to the speaker are short. Wireless handsets and PDAs are great applications for this class-D amplifier to be used without an output filter.

The TPA2038D1 does not require an LC output filter for short speaker connections (approximately 100 mm long or less). A ferrite bead can often be used in the design if failing radiated emissions testing without an LC filter; and, the frequency-sensitive circuit is greater than 1 MHz. If choosing a ferrite bead, choose one with high impedance at high frequencies, but very low impedance at low frequencies. The selection must also take into account the currents flowing through the ferrite bead. Ferrites can begin to loose effectiveness at much lower than rated current values. See the EVM User's Guide (SLOU298) for components used successfully by TI.

Figure 45 shows a typical ferrite-bead output filter.

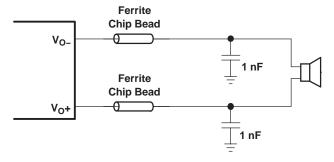


Figure 45. Typical Ferrite Chip Bead Filter

PRINTED CIRCUIT BOARD LAYOUT

In making the pad size for the WCSP balls, it is recommended that the layout use non-solder-mask-defined (NSMD) land. With this method, the solder mask opening is made larger than the desired land area, and the opening size is defined by the copper pad width. Figure 46 shows the appropriate diameters for a WCSP layout.

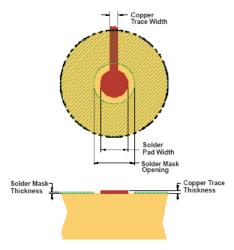


Figure 46. Land Pattern Image and Dimensions

SOLDER PAD DEFINITIONS	COPPER PAD	SOLDER MASK OPENING ⁽⁵⁾	COPPER THICKNESS	STENCIL OPENING ⁽⁶⁾⁽⁷⁾	STENCIL THICKNESS
Non-solder-mask- defined (NSMD)	0.23 mm	0.310 mm	1 oz max (0.032 mm)	0.275 mm x 0.275 mm Sq. (rounded corners)	0.1 mm thick

- 1. Circuit traces from NSMD defined PWB lands should be 75 μ m to 100 μ m wide in the exposed area inside the solder mask opening. Wider trace widths reduce device stand off and impact reliability.
- 2. Best reliability results are achieved when the PWB laminate glass transition temperature is above the operating the range of the intended application.
- 3. Recommend solder paste is Type 3 or Type 4.
- 4. For a PWB using a Ni/Au surface finish, the gold thickness should be less 0.5 mm to avoid a reduction in thermal fatigue performance.
- 5. Solder mask thickness should be less than 20 µm on top of the copper circuit pattern
- 6. Best solder stencil performance is achieved using laser cut stencils with electro polishing. Use of chemically etched stencils give inferior solder paste volume control.
- 7. Trace routing away from WCSP device should be balanced in X and Y directions to avoid unintentional component movement due to solder wetting forces.

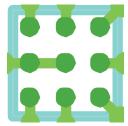


Figure 47. Layout Snapshot

An on-pad via is not required to route the middle ball B2 (PV_{DD}) of the TPA2038D1. Short ball B2 (PV_{DD}) to ball B1 (V_{DD}) and connect both to the supply trace as shown in Figure 47. This simplifies board routing and saves manufacturing cost.



PACKAGE DIMENSIONS

D	E
Max = 1190μm	Max = 1244µm
Min = 1130μm	Min = 1184μm



REVISION HISTORY

CI	hanges from Original (August 2011) to Revision A	Pag	E
•	Changed 说明的第一句,8 欧姆至 4 欧姆		1
•	Changed D and E dimensions in the Package Dimensions table.	1	7



PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

www.ti.com

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPA2038D1YFFR	ACTIVE	DSBGA	YFF	9	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	QWK	Samples
TPA2038D1YFFT	ACTIVE	DSBGA	YFF	9	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	QWK	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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10-Dec-2020

PACKAGE MATERIALS INFORMATION

www.ti.com 19-Jun-2024

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPA2038D1YFFR	DSBGA	YFF	9	3000	180.0	8.4	1.34	1.34	0.81	4.0	8.0	Q1
TPA2038D1YFFT	DSBGA	YFF	9	250	180.0	8.4	1.34	1.34	0.81	4.0	8.0	Q1

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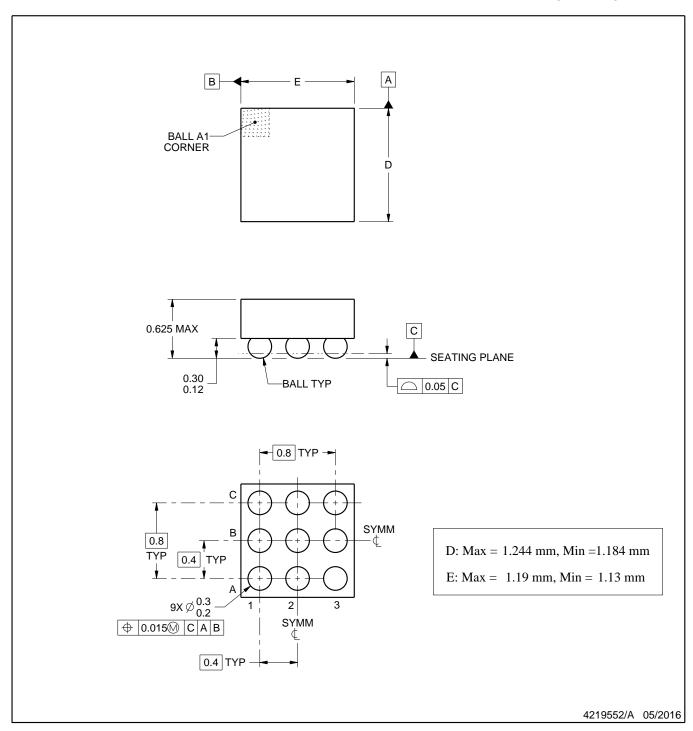


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPA2038D1YFFR	DSBGA	YFF	9	3000	182.0	182.0	20.0
TPA2038D1YFFT	DSBGA	YFF	9	250	182.0	182.0	20.0



DIE SIZE BALL GRID ARRAY



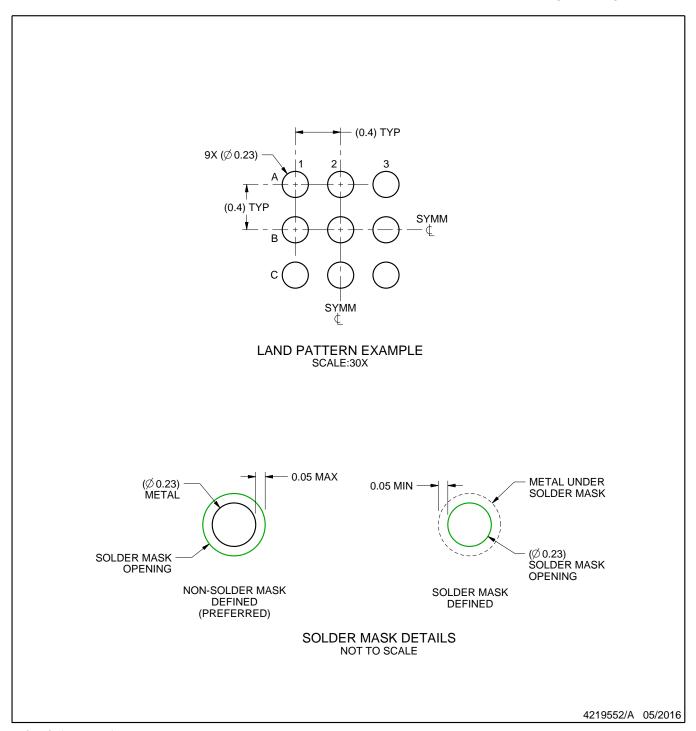
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

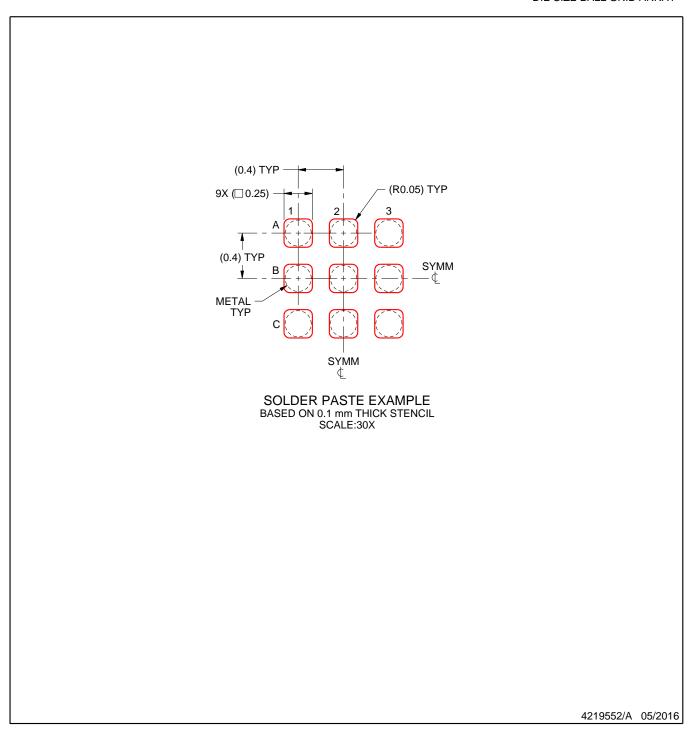


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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